

Vibrational Spectroscopy of Small Silicon-Carbides

DISILICONCARBIDE

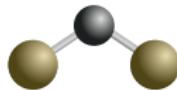
Daniel Witsch
University of Kassel
Laboratory Astrophysics

Sympsium

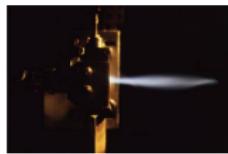
Wuppertal
12.12.2016



1 Introduction



2 The Apparatus

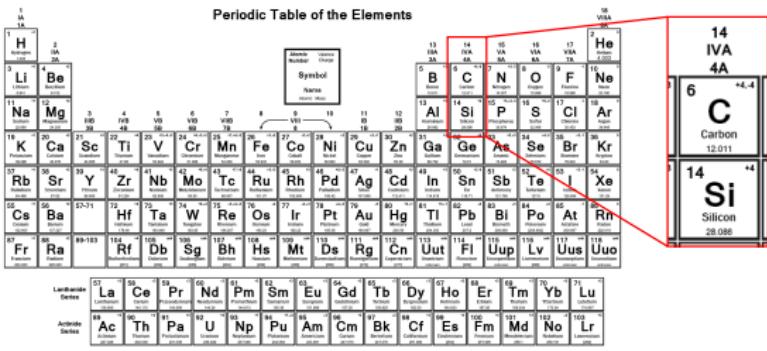


3 Data and Analysis

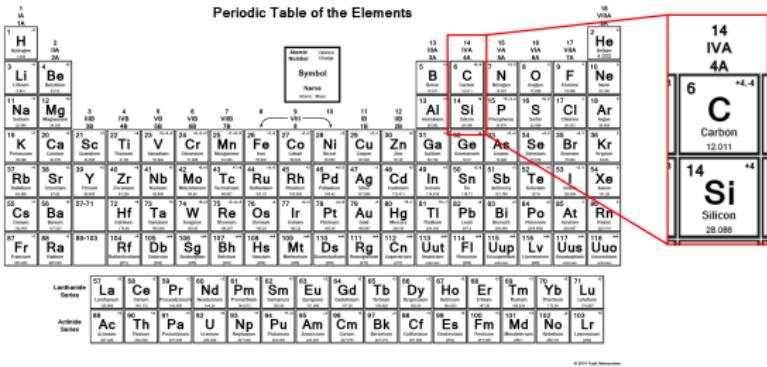


4 Summary

Small Silicon-Carbon Molecules



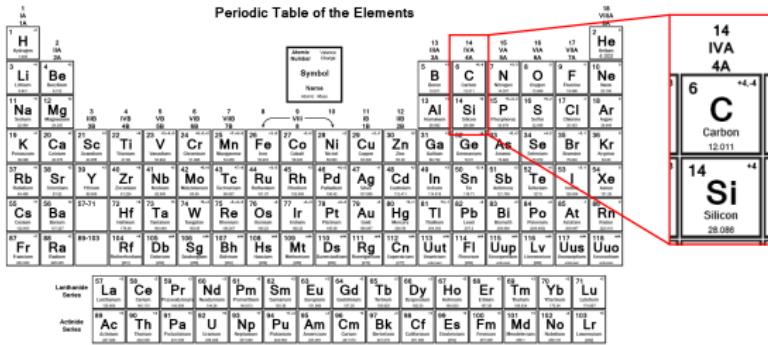
Small Silicon-Carbon Molecules



Bonding properties:

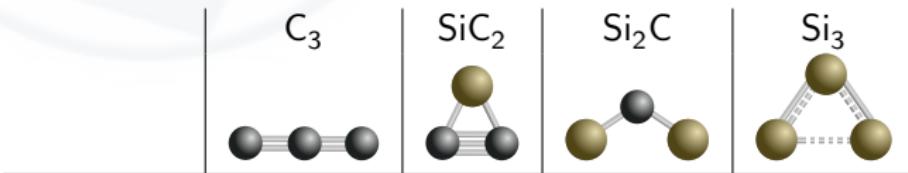
- C: single or multiple bonds
- Si: multidirectional bonds

Small Silicon-Carbon Molecules

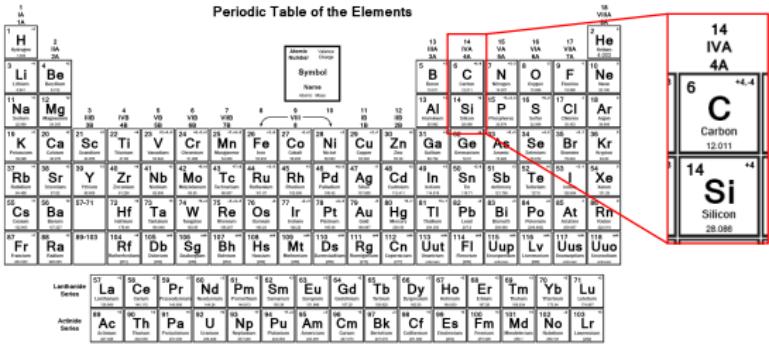


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Small Silicon-Carbon Molecules

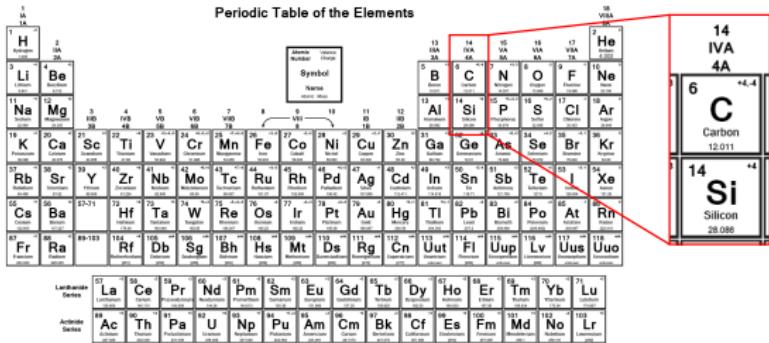


Bonding properties:

- C: single or multiple bonds
- Si: multidirectional bonds

	C_3	SiC_2	Si_2C	Si_3
Rotation	-	✓	✓	✓

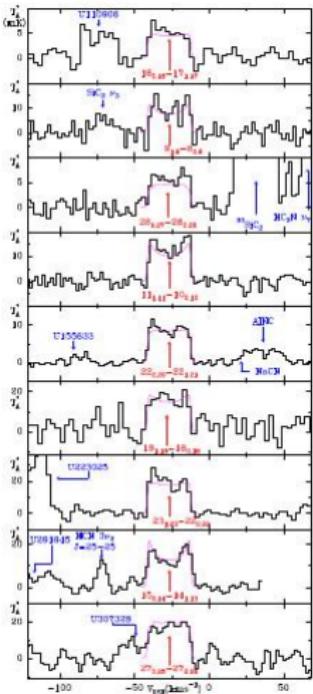
Small Silicon-Carbon Molecules



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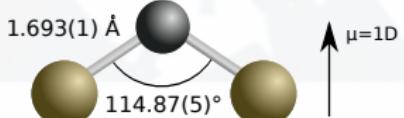
- C: single or multiple bonds
- Si: multidirectional bonds

	C_3	SiC_2	Si_2C	Si_3
Rotation	-	✓	✓	✓
Vibration	✓	✓	✗	✗

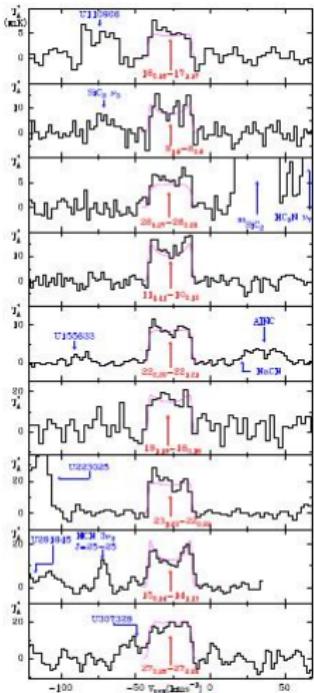


Detection of Si_2C towards
IRC+10216
J. Cernicharo et. al., Ap.J.Lett. L3 2015

Vibrational Groundstate Structure



M.C. McCarthy et. al., J.Phys.Chem.Lett 6 (2015), 2107

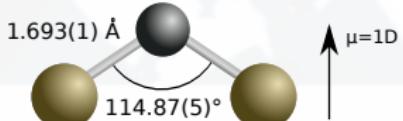


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J. Cernicharo et. al., Ap.J.Lett. L3 2015

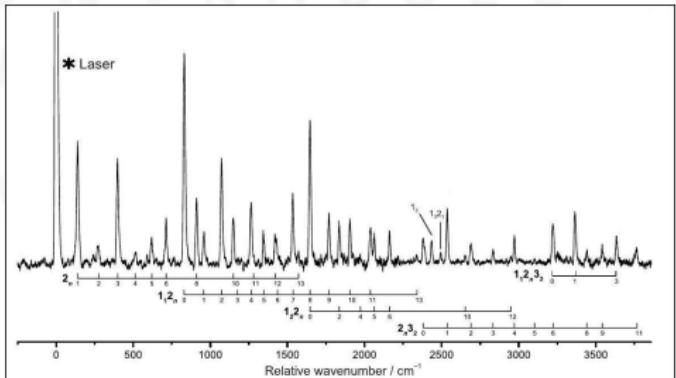
Disiliconcarbide (Si_2C)



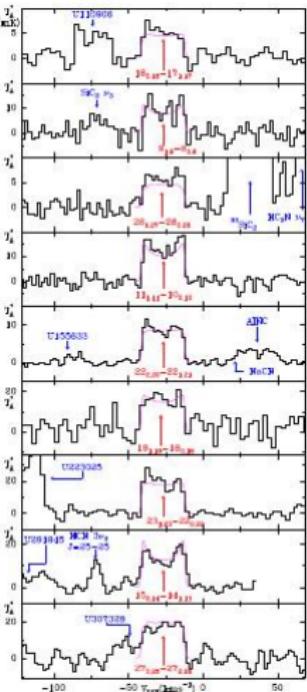
Vibrational Groundstate Structure



M.C. McCarthy et. al., J.Phys.Chem.Lett 6 (2015), 2107



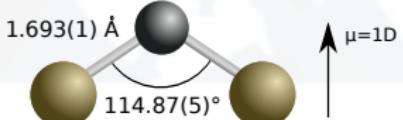
M.C. McCarthy et. al., J.Phys.Chem. 142 (2015), 231101



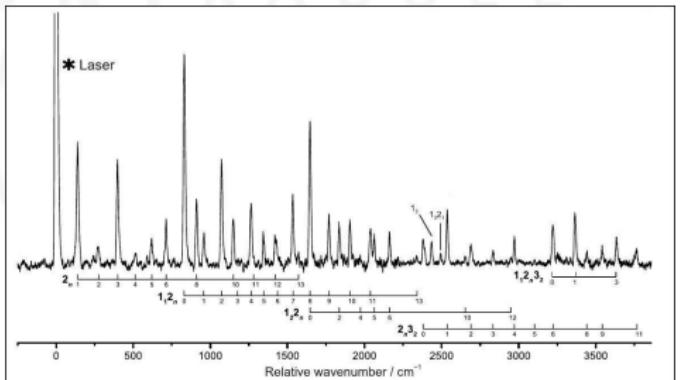
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Disiliconcarbide (Si_2C)

Vibrational Groundstate Structure



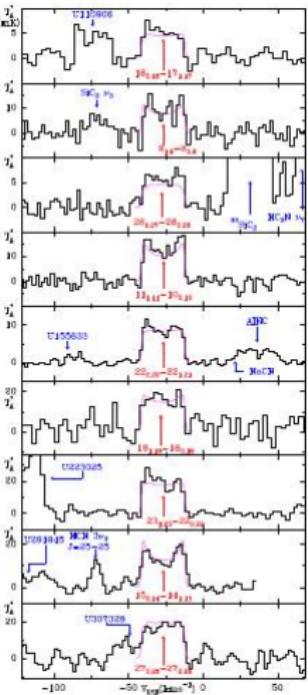
M.C. McCarthy et. al., J.Phys.Chem.Lett 6 (2015), 2107



M.C. McCarthy et. al., J.Phys.Chem. 142 (2015), 231101

	ν_1	ν_2	ν_3
Frequency [cm ⁻¹]	143	831	1198
Calculated ^b [cm ⁻¹]	142	838	1207
Intensity ^b [km/mol]	1.0	16.5	198.2

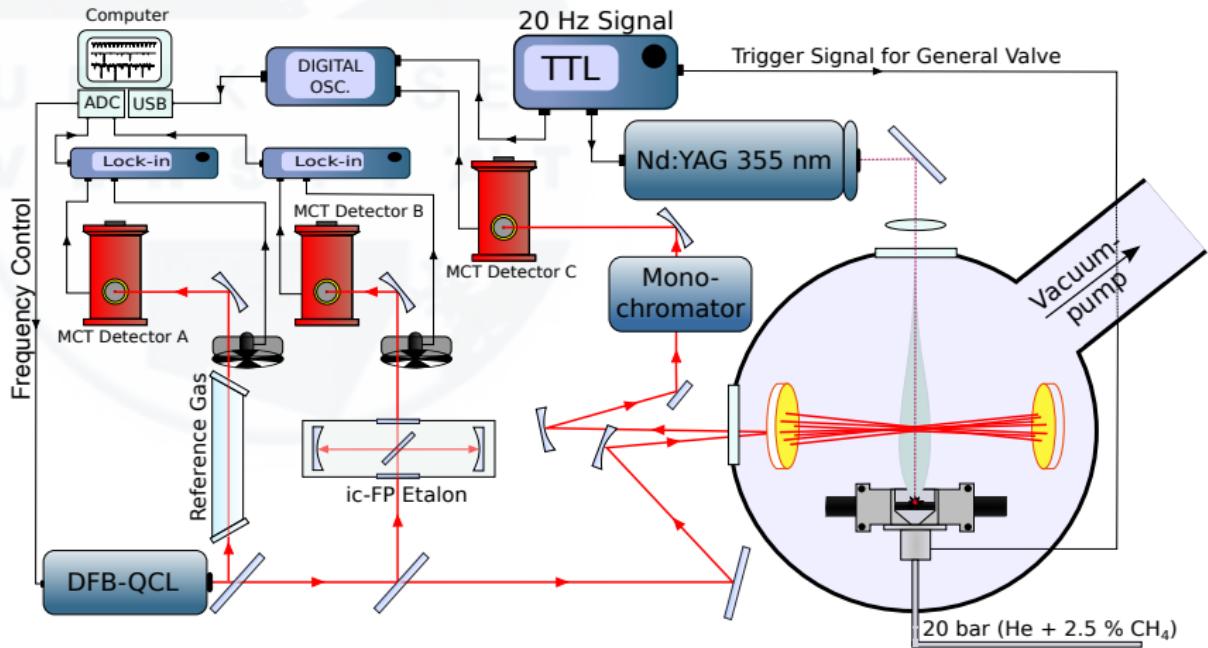
^b from CCSD(T)/cc-pwCVQZ calculations (S. Thorwirth)



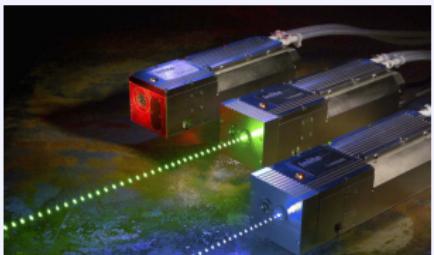
Detection of Si_2C towards
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The Apparatus



Pulsed Nd:YAG



www.continuumlasers.com

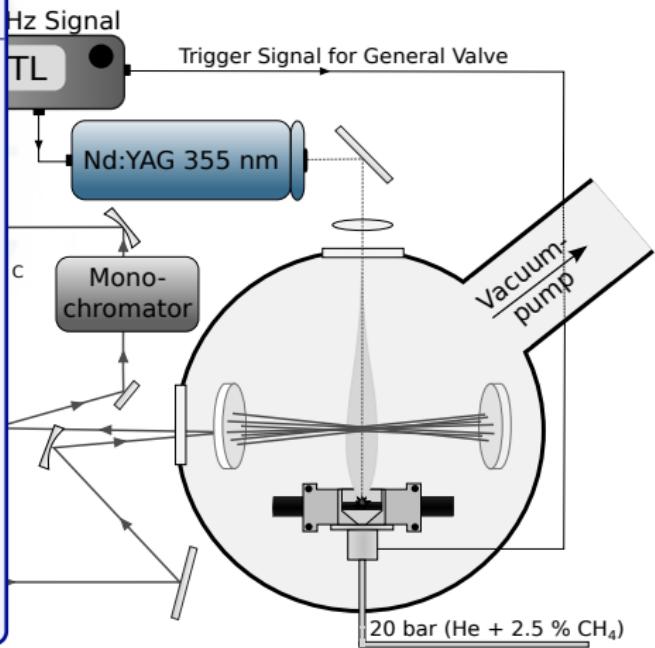
Details

Wavelength 355 nm

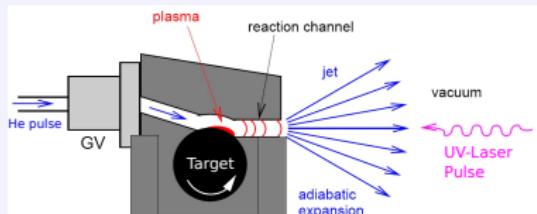
Pulse energy 40 mJ

Repetition rate 20 Hz

Pulse length 7 - 9 ns



Cluster Source



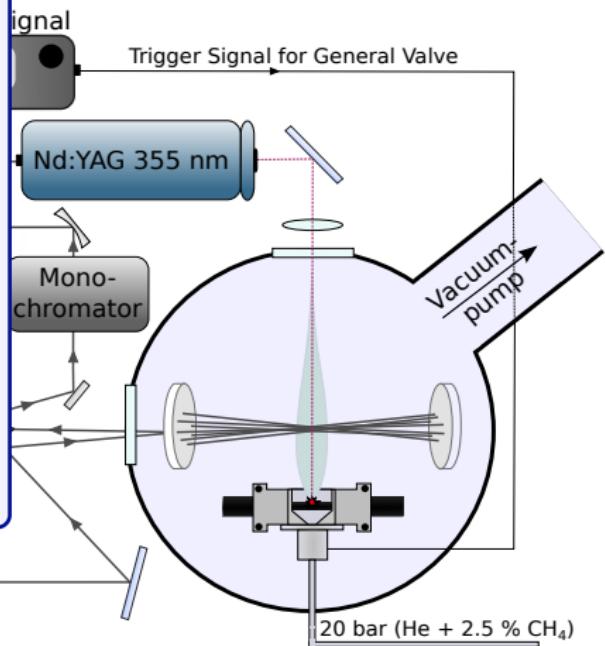
Details

Rot. Temperature $\sim 30\text{ K}$

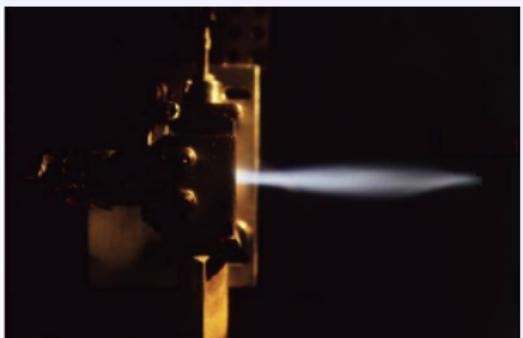
Target Material Si

Buffergas He + 2.5 % CH₄

Backing Pressure 20 bar



Cluster Source



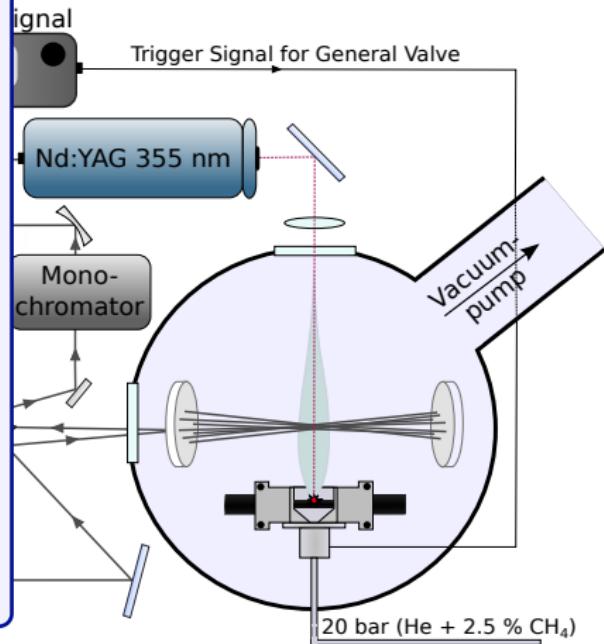
Details

Rot. Temperature ~ 30 K

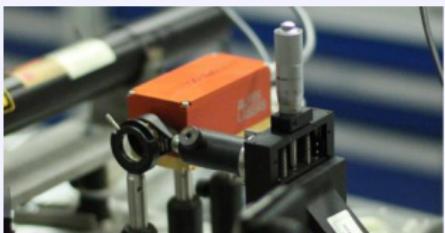
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Quantum Cascade Laser



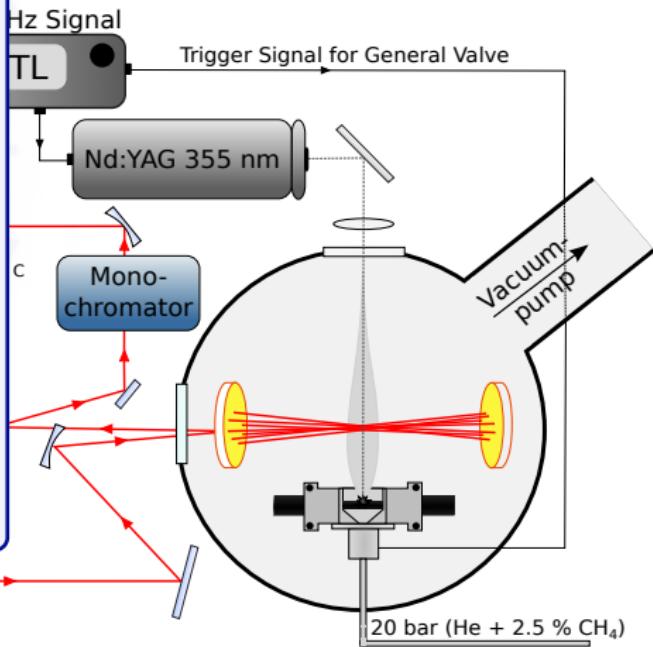
Details

Frequency $1208 - 1217 \text{ cm}^{-1}$

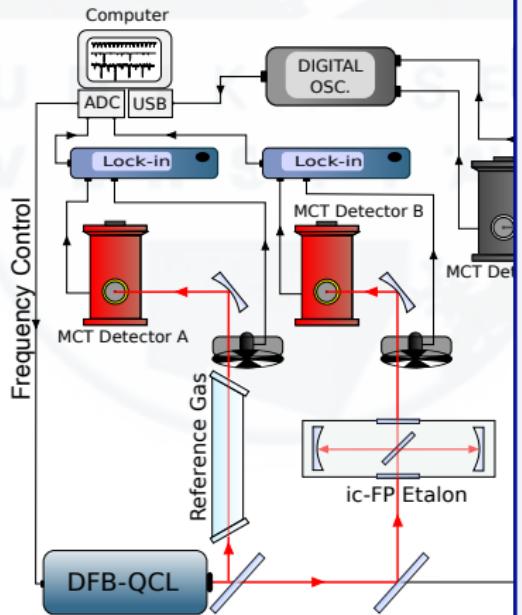
Power (cw) up to 20 mW

Herriott-type multi-pass optics
with up to 50 passes

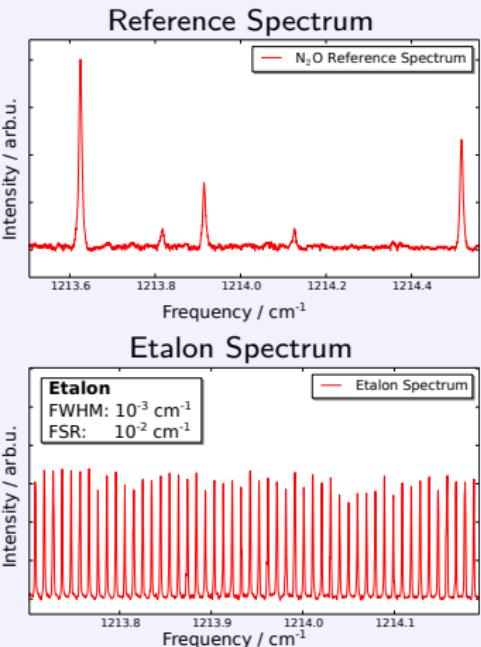
DFB-QCL



The Apparatus

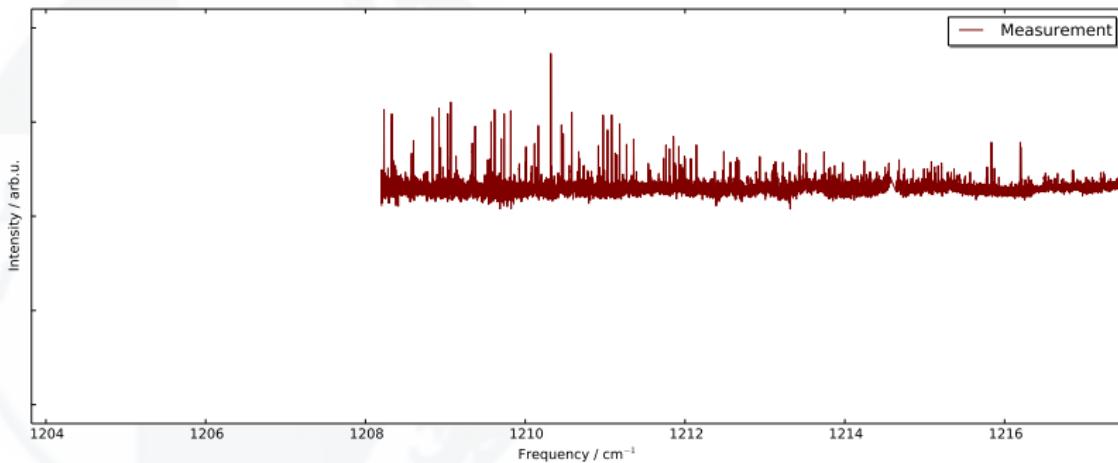


Frequency Calibration



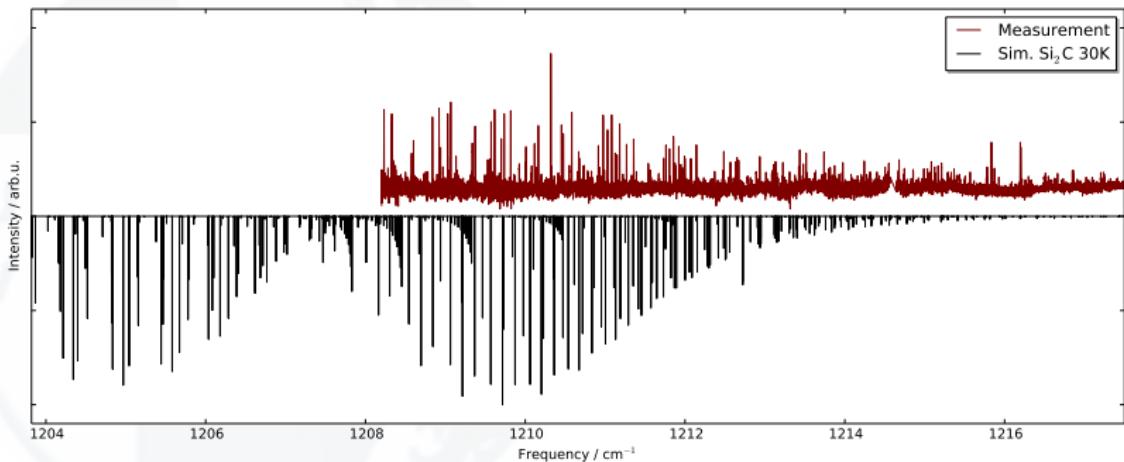
Calibration Accuracy: $\Delta\nu \approx 10^{-4} \text{ cm}^{-1}$

Rovibrational Spectrum of a Silicon-Carbide



- 120 absorption features
- Calculated band origin^b
 $\nu_3 = 1207.34 \text{ cm}^{-1}$
- D's, H's taken from J. Chernicharo *et. al.*
- Assignment needed

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Molecular Constants of Si₂C

	Ground ^a	$\nu_3 = 1^b$
A	64074.3366(44)	60347.75
B	4395.51772(41)	4463.64
C	4102.13098(62)	4156.22

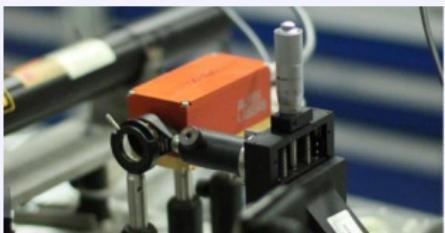
values in MHz

^a J. Chernicharo *et. al.*, Ap.J.Lett. L3 2015

^b α_i from CCSD(T)/cc-pwCVQZ calculations (S. Thorwirth)

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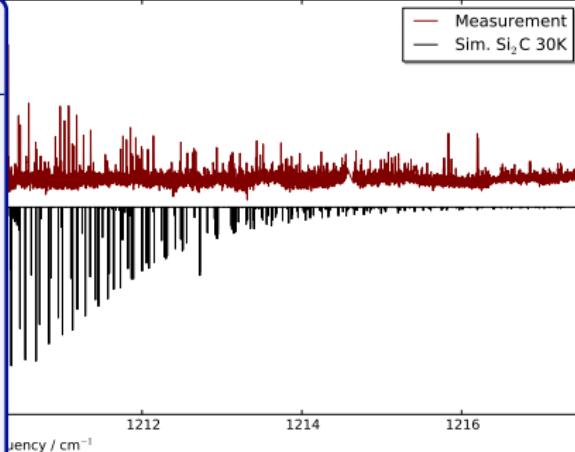
Quantum Cascade Laser



Details

Frequency $1200 - 1208 \text{ cm}^{-1}$

Power (cw) up to 100 mW



- Calculated band origin^b
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- Assignment needed

Molecular Constants of Si_2C

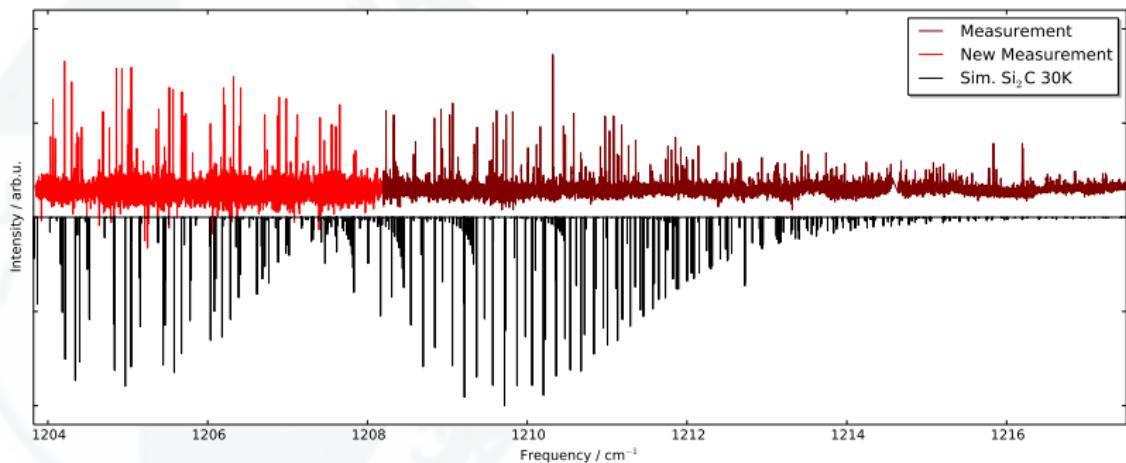
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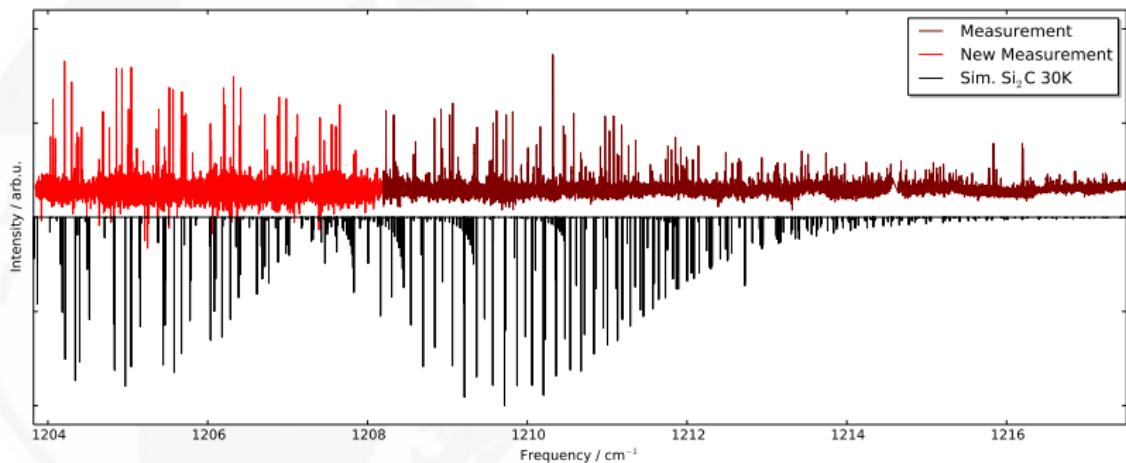
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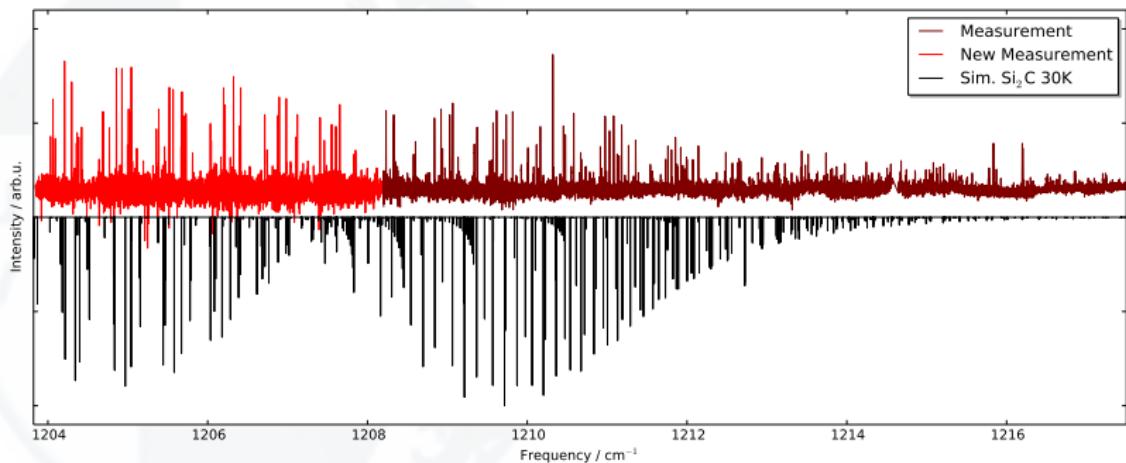
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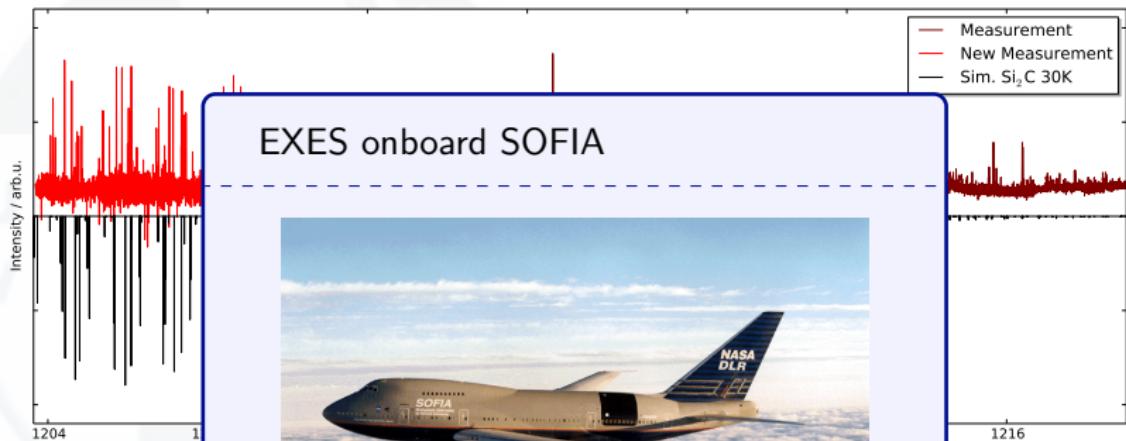
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- 120 absop
- Calculated
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Assignments of Si_2C

$$\nu_3 = 1^b$$

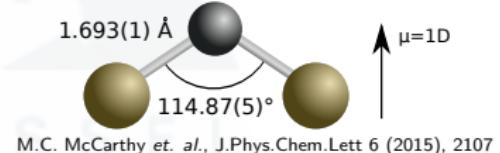
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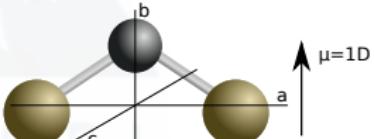
Vibrational Groundstate Structure



M.C. McCarthy *et. al.*, J.Phys.Chem.Lett 6 (2015), 2107

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VERSITÄT

Vibrational Groundstate Structure

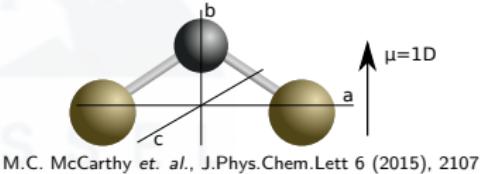


M.C. McCarthy et. al., J.Phys.Chem.Lett 6 (2015), 2107

What do we know?

- electronic ground state: 1A_1
- $I(\text{Si}) = 0$ symmetric spin wavefunction
- asymmetric stretching vibration (vib. excited state: B_2 symmetry)
- a-type transition ($\Delta K_a = 0$ and $\Delta K_c = \pm 1$)

Vibrational Groundstate Structure

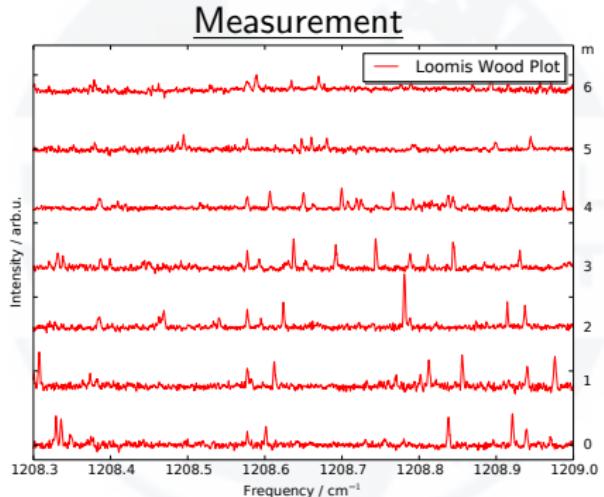


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Similar Systems?

- H_2O ?
 - similar structure
 - BUT mass in O-atom
- Cl_2O
 - Distortion due to coupling with symmetric stretching vibration

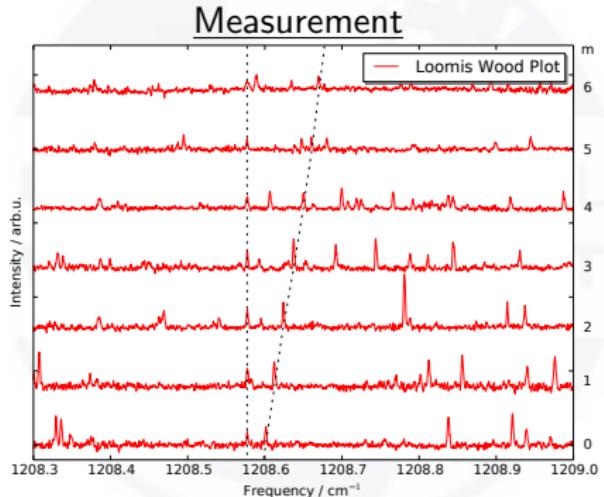


several series have been found

$$\text{Shift} = b \cdot m + d \cdot m^2$$

$$b \approx 0.74 \text{ cm}^{-1}$$

$$d \approx 0.01 \text{ cm}^{-1}$$

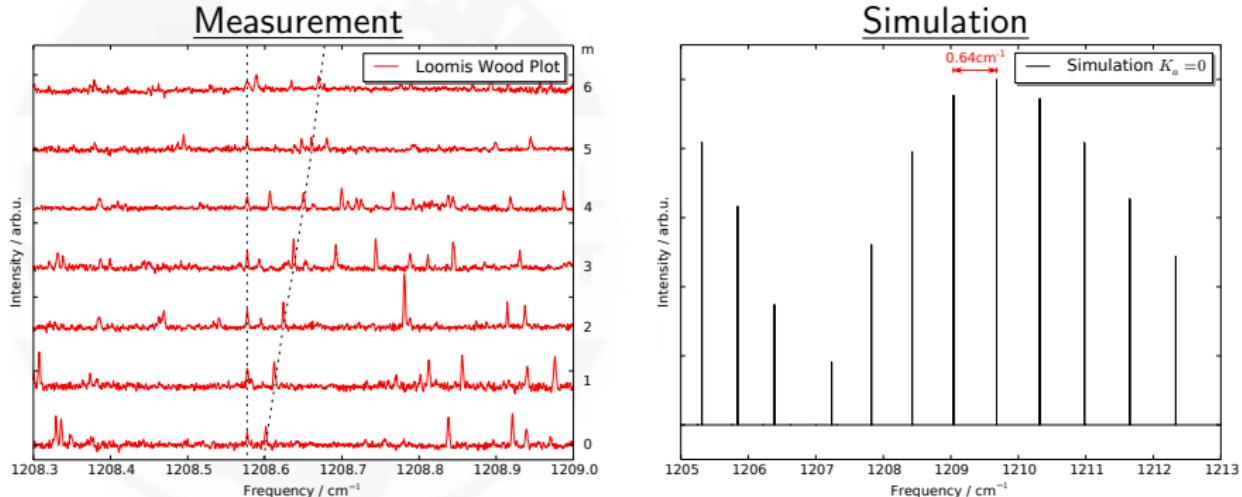


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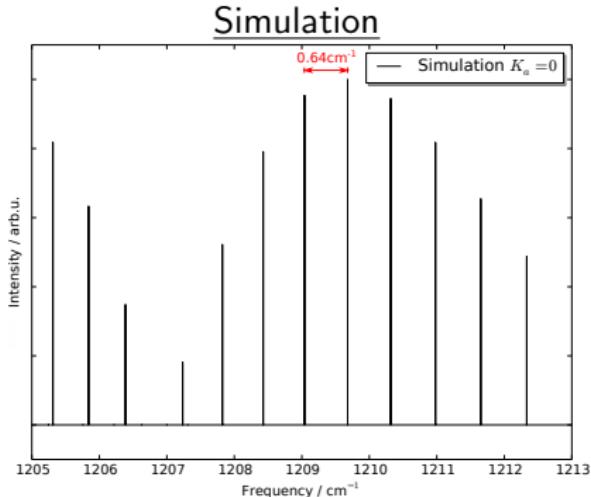
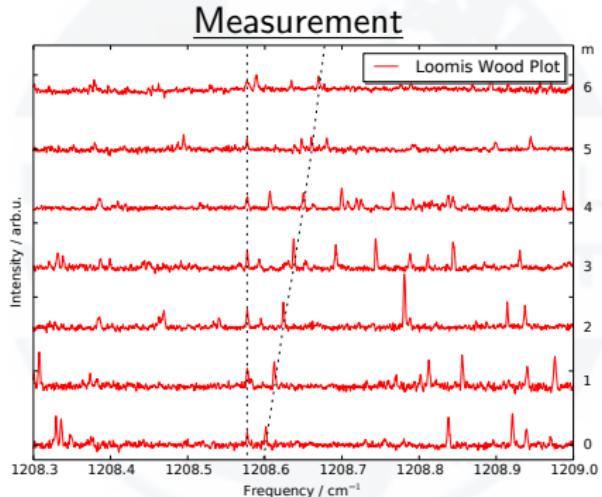


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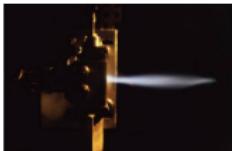
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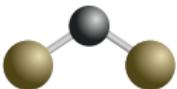
$$b \approx 0.74 \text{ cm}^{-1}$$

$$d \approx 0.01 \text{ cm}^{-1}$$

- B'' and C'' seem to be larger than calculated values
- Different Shifts between series ($0.68 < \frac{b}{\text{cm}^{-1}} < 0.8 \Rightarrow$ Distortion?)
- Assignment needed:
 - New PGopher feature



- Experimental setup to produce cold and small silicon-carbides
- Rovibrational spectrum of the ν_3 band of Si_2C
- B'' and C'' are 1 to 3 % larger than calculated values for Si_2C
- Prepared for interstellar search with EXES onboard SOFIA

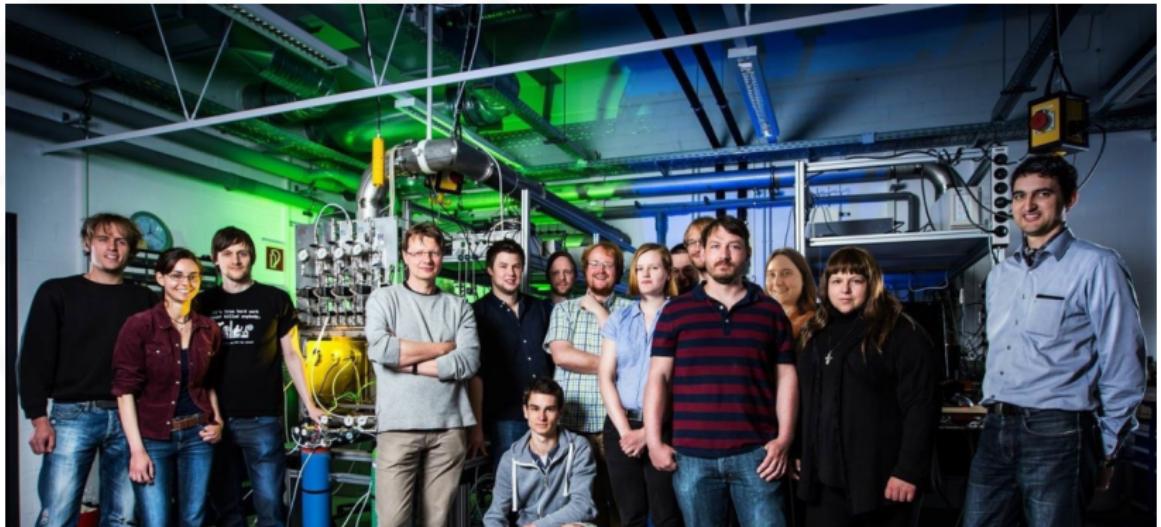


Acknowledgement

- **Jürgen Gauss** (University of Mainz)
- **Sven Thorwirth** (University of Cologne)



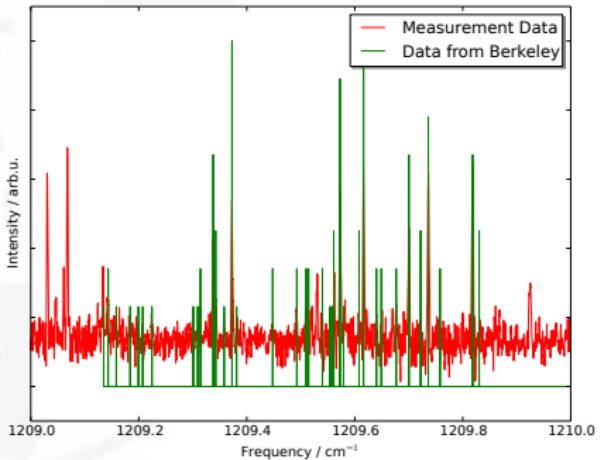
Funding by
DFG Deutsche
Forschungsgemeinschaft



Thank you for your attention!



Appendix



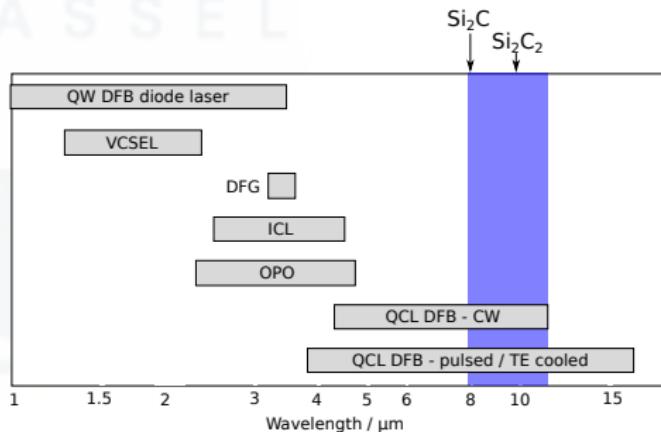
Berkeley:

- Ablation Laser: Excimer Laser
- Silicon-Carbide (SiC) Rod
- pure Helium Carrier-Gas

Kassel:

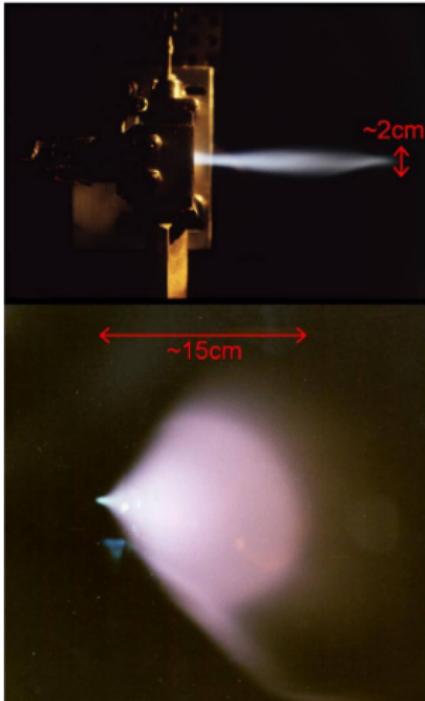
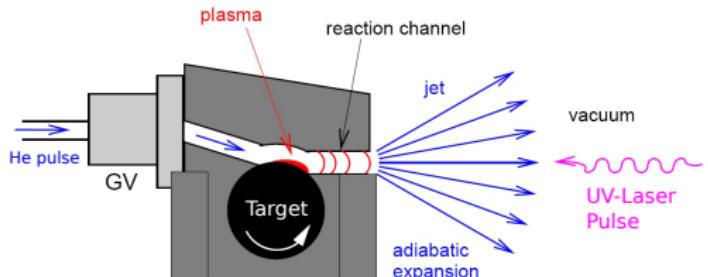
- Ablation Laser: Nd:YAG
- pure Silicon (Si) Rod
- Carrier-Gas: 2.5% CH₄ in Helium

- Asymmetric stretching vibration of Si_2C expected to be at $8 \mu\text{m}$ (1250 cm^{-1})
- Common radiation sources for IR-spectroscopy



Hodgkinson *et al.*, Meas. Sci. Technol. 24 (2013)

- Lack of radiation sources above $5 \mu\text{m}$
- Two main tasks: Production and Investigation



Laser Ablation Source

Laserfrequency	355 nm
Pulse energy	40 mJ
Repetition rate	20 Hz
Helium gas	20 bar
Background pressure	0.1 mbar
Target material	SiC